

# PMBFJ111; PMBFJ112; PMBFJ113 N-channel junction FETs

Rev. 4 — 20 September 2011

**Product data sheet** 

#### **Product profile** 1.

### **1.1 General description**

Symmetrical N-channel junction FETs in a SOT23 package.

### 1.2 Features and benefits

- High-speed switching
- Interchangeability of drain and source connections
- Low  $R_{DSon}$  at zero gate voltage (< 30  $\Omega$  for PMBFJ111).

### 1.3 Applications

- Analog switches
- Choppers
- Commutators
- Multiplexers
- Thin and thick film hybrids.

#### **Pinning information** 2.

Pin	Description <sup>[1]</sup>	Simplified outline	Symbol
1	drain		
2	source		
3	gate		3 → 1 2 sym053

[1] Drain and source are interchangeable.



**N-channel junction FETs** 

### 3. Ordering information

Table 2.         Ordering information							
Type number	Package	ackage					
	Name	Description	Version				
PMBFJ111	-	plastic surface mounted package; 3 leads	SOT23				
PMBFJ112							
PMBFJ113							

### 4. Marking

Table 3. Marking	
Type number	Marking code <sup>[1]</sup>
PMBFJ111	41*
PMBFJ112	42*
PMBFJ113	47*

[1] \* = p: Made in Hong Kong

\* = t: Made in Malaysia

\* = W: Made in China

### 5. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage (DC)		-	±40	V
V <sub>GSO</sub>	gate-source voltage		-	-40	V
$V_{GDO}$	gate-drain voltage		-	-40	V
l <sub>G</sub>	forward gate current (DC)		-	50	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} = 25 \ ^{\circ}C$	<u>[1]</u> _	300	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C

[1] Mounted on a ceramic substrate, 8 mm  $\times$  10 mm  $\times$  0.7 mm.

### 6. Thermal characteristics

#### Table 5. Thermal characteristics

 $T_{i} = P (R_{th(i-t)} + R_{th(t-s)} + R_{th(s-a)}) + T_{amb}.$ 

Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient		<u>[1]</u> 430	K/W
	thermal resistance from junction to ambient		<mark>[2]</mark> 500	K/W

[1] Mounted on a ceramic substrate, 8 mm  $\times$  10 mm  $\times$  0.7 mm.

[2] Mounted on printed circuit board.

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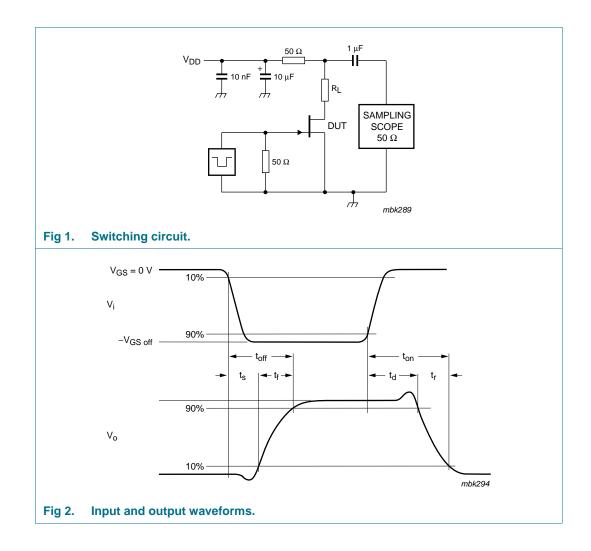
### 7. Static characteristics

Static characteristics					
Parameter	Conditions	Min	Тур	Max	Unit
gate-source leakage current	$V_{GS} = -15 \text{ V};  V_{DS} = 0 \text{ V}$	-	-	-1	nA
drain-source leakage current					
PMBFJ111	$V_{GS} = 0 V; V_{DS} = 15 V$	20	-	-	mA
PMBFJ112	$V_{GS} = 0 V; V_{DS} = 15 V$	5	-	-	mA
PMBFJ113	$V_{GS} = 0 V; V_{DS} = 15 V$	2	-	-	mA
gate-source breakdown voltage	$I_G = -1 \ \mu A; \ V_{DS} = 0 \ V$	-40	-	-	V
gate-source cut-off voltage					
PMBFJ111	$I_{D} = 1 \ \mu A; \ V_{DS} = 5 \ V$	-10	-	-3	V
PMBFJ112	$I_{D} = 1 \ \mu A; \ V_{DS} = 5 \ V$	-5	-	-1	V
PMBFJ113	$I_{D} = 1 \ \mu A; \ V_{DS} = 5 \ V$	-3	-	-0.5	V
drain-source on-state resistance					
PMBFJ111	$V_{GS} = 0 \text{ V}; V_{DS} = 0.1 \text{ V}$	-	-	30	Ω
PMBFJ112	$V_{GS} = 0 \text{ V}; V_{DS} = 0.1 \text{ V}$	-	-	50	Ω
PMBFJ113	$V_{GS} = 0 V; V_{DS} = 0.1 V$	-	-	100	Ω
	Parametergate-source leakage currentdrain-source leakage currentPMBFJ111PMBFJ112PMBFJ113gate-source breakdown voltagegate-source cut-off voltagePMBFJ111PMBFJ112PMBFJ113drain-source on-state resistancePMBFJ111PMBFJ111PMBFJ111PMBFJ111PMBFJ111PMBFJ111PMBFJ112PMBFJ111PMBFJ112	ParameterConditionsgate-source leakage current $V_{GS} = -15 \text{ V}; V_{DS} = 0 \text{ V}$ drain-source leakage current $V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$ PMBFJ111 $V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$ PMBFJ112 $V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$ PMBFJ113 $V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$ gate-source breakdown voltage $I_G = -1 \mu A; V_{DS} = 0 \text{ V}$ gate-source cut-off voltage $I_D = 1 \mu A; V_{DS} = 5 \text{ V}$ PMBFJ112 $I_D = 1 \mu A; V_{DS} = 5 \text{ V}$ PMBFJ113 $I_D = 1 \mu A; V_{DS} = 5 \text{ V}$ drain-source on-state resistance $P$ MBFJ111PMBFJ112 $V_{GS} = 0 \text{ V}; V_{DS} = 0.1 \text{ V}$ PMBFJ112 $V_{GS} = 0 \text{ V}; V_{DS} = 0.1 \text{ V}$	Parameter         Conditions         Min           gate-source leakage current $V_{GS} = -15 V; V_{DS} = 0 V$ -           drain-source leakage current $V_{GS} = 0 V; V_{DS} = 15 V$ 20           PMBFJ111 $V_{GS} = 0 V; V_{DS} = 15 V$ 20           PMBFJ112 $V_{GS} = 0 V; V_{DS} = 15 V$ 5           PMBFJ113 $V_{GS} = 0 V; V_{DS} = 15 V$ 2           gate-source breakdown voltage $I_G = -1 \mu A; V_{DS} = 0 V$ -40           gate-source cut-off voltage $I_G = -1 \mu A; V_{DS} = 5 V$ -10           PMBFJ111 $I_D = 1 \mu A; V_{DS} = 5 V$ -5           PMBFJ113 $I_D = 1 \mu A; V_{DS} = 5 V$ -3           drain-source on-state resistance $PMBFJ111$ $V_{GS} = 0 V; V_{DS} = 0.1 V$ -           PMBFJ112 $V_{GS} = 0 V; V_{DS} = 0.1 V$ -         -	Parameter         Conditions         Min         Typ           gate-source leakage current $V_{GS} = -15 \text{ V}; V_{DS} = 0 \text{ V}$ -         -           drain-source leakage current $V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$ 20         -           PMBFJ111 $V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$ 20         -           PMBFJ112 $V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$ 5         -           PMBFJ113 $V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$ 2         -           gate-source breakdown voltage $I_G = -1 \mu A; V_{DS} = 0 \text{ V}$ -40         -           gate-source cut-off voltage         -         -         -         -           PMBFJ111 $I_D = 1 \mu A; V_{DS} = 5 \text{ V}$ -10         -           PMBFJ113 $I_D = 1 \mu A; V_{DS} = 5 \text{ V}$ -5         -           PMBFJ113 $I_D = 1 \mu A; V_{DS} = 5 \text{ V}$ -3         -           drain-source on-state resistance         -         -         -           PMBFJ112 $V_{GS} = 0 \text{ V}; V_{DS} = 0.1 \text{ V}$ -         -           PMBFJ112 $V_{GS} = 0 \text{ V}; V_{DS} = 0.1 \text{ V}$ -         -	ParameterConditionsMinTypMaxgate-source leakage current $V_{GS} = -15 V; V_{DS} = 0 V$ 1drain-source leakage current $V_{GS} = 0 V; V_{DS} = 15 V$ 201PMBFJ111 $V_{GS} = 0 V; V_{DS} = 15 V$ 20PMBFJ112 $V_{GS} = 0 V; V_{DS} = 15 V$ 5PMBFJ113 $V_{GS} = 0 V; V_{DS} = 15 V$ 2gate-source breakdown voltage $I_G = -1 \mu A; V_{DS} = 0 V$ -40gate-source cut-off voltage $U_D = 1 \mu A; V_{DS} = 5 V$ -103-PMBFJ112 $I_D = 1 \mu A; V_{DS} = 5 V$ -51PMBFJ113 $I_D = 1 \mu A; V_{DS} = 5 V$ -30.5drain-source on-state resistance $V_{GS} = 0 V; V_{DS} = 0.1 V$ 3050PMBFJ112 $V_{GS} = 0 V; V_{DS} = 0.1 V$ 50

### 8. Dynamic characteristics

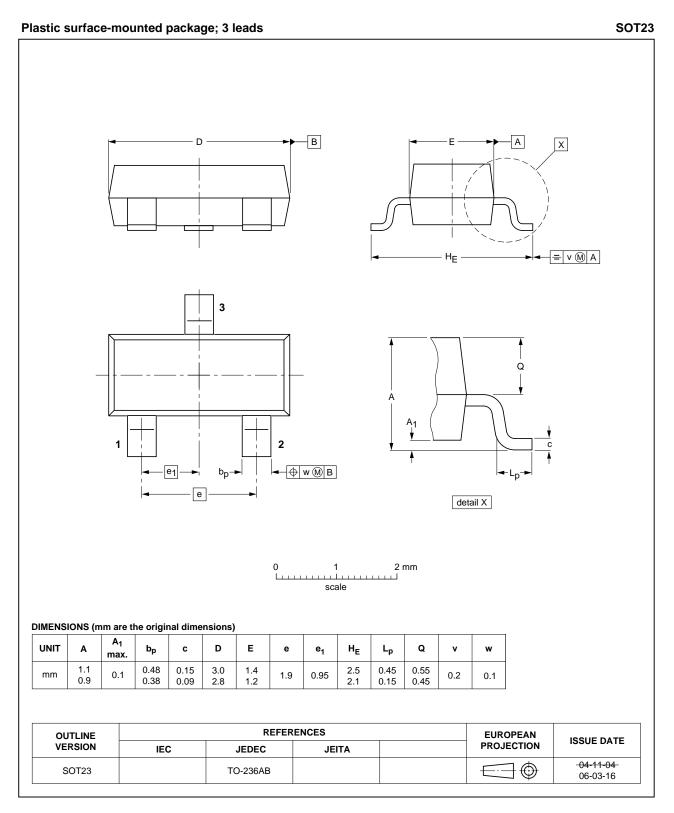
Table 7.	Dynamic characteristics					
Symbol	Parameter Conditions				Max	Unit
C <sub>iss</sub>	input capacitance	$V_{DS}$ = 0 V; $V_{GS}$ = -10 V; f = 1 MHz	-	6	-	pF
		$V_{DS}$ = 0 V; $V_{GS}$ = 0 V; f = 1 MHz; $T_{amb}$ = 25 °C	-	22	28	pF
C <sub>rss</sub>	feedback capacitance		-	3	-	pF
Switching	times; see Figure 2					
t <sub>r</sub>	rise time		<u>[1]</u> -	6	-	ns
t <sub>on</sub>	turn-on time		<u>[1]</u> -	13	-	ns
t <sub>f</sub>	fall time		<u>[1]</u> -	15	-	ns
t <sub>off</sub>	turn-off time		<u>[1]</u> -	35	-	ns

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### 9. Package outline



### Fig 3. Package outline.

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PMBFJ111\_112\_113

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### **10. Revision history**

Table 8.Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes
PMBFJ111_112_113 v.4	20110920	Product data sheet	-	PMBFJ111_112_113 v.3
Modifications:	guidelines o Legal texts	of NXP Semiconductors.	ne new company n	comply with the new identity ame where appropriate. atest version.
PMBFJ111_112_113 v.3 (9397 750 13402)	20040804	Product data sheet	-	PMBFJ111_112_113_CNV v.2
PMBFJ111_112_113_CNV v.2	19971201	Product specification	-	-

### 11. Legal information

### 11.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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